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PATENT  
740756-1638

THE UNITED STATES PATENT AND TRADEMARK OFFICE

#49/K  
7/11/02  
Hayes

In re PATENT application of:

Hisashi OHTANI et al.

Application No.: 08/807,737

Filed: February 27, 1997

For: METHOD FOR MANUFACTURING  
SEMICONDUCTOR DEVICE

)  
)  
) Art Unit: 2813  
)  
) Examiner: Evan T. PERT

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AMENDMENT

Commissioner for Patents  
Washington, D.C. 20231

March 19, 2002

Dear Sir:

In response to the Examiner's non-Final Office Action mailed December 19, 2001 please  
consider the following amendment and remarks in connection with the above identified  
application.

IN THE CLAIMS:

Please amend claim 84 as follows:

KL  
84. (Twice Amended) A method of manufacturing a semiconductor device comprising  
the steps of:  
forming a silicon nitride film containing at least one of hydrogen and oxygen over  
a substrate;  
depositing a semiconductor film comprising amorphous silicon on said silicon  
nitride film;  
disposing a metal in contact with at least a selected portion of said semiconductor  
film;  
heating said semiconductor film and said metal to crystallize said semiconductor  
film; and  
forming a channel region,

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